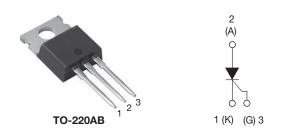
Vishay Semiconductors

High Voltage, Phase Control Thyristor, 12 A



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PRIMARY CHARACTERISTICS							
I _{T(AV)}	8 A						
V _{DRM} /V _{RRM}	800 V						
V _{TM}	1.2 V						
I _{GT}	15 mA						
TJ	-40 to +125 °C						
Package	TO-220AB						
Circuit configuration	Single SCR						

FEATURES

- AEC-Q101 qualified
- Meets JESD 201 class 1A whisker test
- Flexible solution for reliable AC power rectification
- Easy control peak current at charger power up to reduce passive / electromechanical components
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

APPLICATIONS

- On-board and off-board EV / HEV battery chargers
- Renewable energy inverters

DESCRIPTION

The VS-12TTS08HM3 high voltage series of silicon controlled rectifiers are specifically designed for medium power switching and phase control applications.

OUTPUT CURRENT IN TYPICAL APPLICATIONS							
APPLICATIONS	SINGLE-PHASE BRIDGE	THREE-PHASE BRIDGE	UNITS				
Capacitive input filter $T_A = 55$ °C, $T_J = 125$ °C, common heatsink of 1 °C/W	13.5	17	А				

MAJOR RATINGS AND CHARACTERISTICS									
PARAMETER	TEST CONDITIONS	VALUES	UNITS						
I _{T(AV)}	Sinusoidal waveform	8	•						
I _{T(RMS)}		12.5	A						
V _{RRM} /V _{DRM}		800	V						
I _{TSM}		110	A						
V _T	8 A, T _J = 25 °C	1.2	V						
dV/dt		150	V/µs						
dl/dt		100	A/µs						
TJ	Range	-40 to +125	°C						

VOLTAGE RATINGS									
PART NUMBER	V _{RRM} , MAXIMUM PEAK REVERSE VOLTAGE V	V _{DRM} , MAXIMUM PEAK DIRECT VOLTAGE V	I _{RRM} / I _{DRM} AT 125 °C mA						
VS-12TTS08HM3	800	800	5.0						

(Pb) RoHS

COMPLIANT HALOGEN

VS-12TTS08HM3



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ABSOLUTE MAXIMUM RATINGS	;			
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum average on-state current	I _{T(AV)}	T = 108 °C 180° conduction half size wave	8	
Maximum RMS on-state current	I _{T(RMS)}	$T_{C} = 108 \ ^{\circ}C$, 180° conduction, half sine wave	12.5	А
Maximum peak one-cycle	L	10 ms sine pulse, rated V_{RRM} applied, T_J = 125 °C	95	A
non-repetitive surge current	I _{TSM}	10 ms sine pulse, no voltage reapplied, T_J = 125 °C	110	
Maximum I ² t for fusing	l ² t	10 ms sine pulse, rated V_{RRM} applied, T_J = 125 °C	45	A ² s
	1-1	10 ms sine pulse, no voltage reapplied, T_J = 125 °C	64	
Maximum I ² √t for fusing	l²√t	t = 0.1 ms to 10 ms, no voltage reapplied, T_{J} = 125 $^{\circ}\text{C}$	640	A²√s
Maximum on-state voltage drop	V _{TM}	8 A, T _J = 25 °C	1.2	V
On-state slope resistance	r _t	Т, ₁ = 125 °С	16.2	mΩ
Threshold voltage	V _{T(TO)}	13 - 123 0	0.87	V
Maximum reverse and direct leakage current	I _{RM} /I _{DM}	$T_J = 25 \degree C$ $V_B = rated V_{BBM} / V_{DBM}$	0.05	
Maximum reverse and direct leakage current	'RM' 'DM	$T_J = 125 \text{ °C}$	5.0	
Typical holding current	Ι _Η	Anode supply = 6 V, resistive load, initial I_T = 1 A, T_J = 25 °C	30	mA
Typical latching current	١L	Anode supply = 6 V, resistive load, T_J = 25 °C	50	
Maximum rate of rise of off-state voltage	dV/dt	$T_J = T_J max.$, linear to 80 %, $V_{DRM} = R_g - k = open$	150	V/µs
Maximum rate of rise of turned-on current	dl/dt		100	A∕µs

TRIGGERING					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Maximum peak gate power	P _{GM}		8.0	W	
Maximum average gate power	P _{G(AV)}		2.0	vv	
Maximum peak positive gate current	+I _{GM}		1.5	А	
Maximum peak negative gate voltage	-V _{GM}		10	V	
		Anode supply = 6 V, resistive load, $T_J = -65 \text{ °C}$	20	mA	
Maximum required DC gate current to trigger	I _{GT}	Anode supply = 6 V, resistive load, $T_J = 25 \text{ °C}$	15		
		Anode supply = 6 V, resistive load, $T_J = 125 \text{ °C}$	10		
		Anode supply = 6 V, resistive load, $T_J = -65 \ ^{\circ}C$	1.2		
Maximum required DC gate voltage to trigger	V_{GT}	Anode supply = 6 V, resistive load, $T_J = 25 \text{ °C}$	1		
		Anode supply = 6 V, resistive load, $T_J = 125 \text{ °C}$	0.7	V	
Maximum DC gate voltage not to trigger	V _{GD}	T 105 °C V reteductus	0.2		
Maximum DC gate current not to trigger	I _{GD}	T _J = 125 °C, V _{DRM} = rated value	0.1	mA	

SWITCHING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Typical turn-on time	t _{gt}	T _J = 25 °C	0.8	
Typical reverse recovery time	t _{rr}	T _{.1} = 125 °C	3	μs
Typical turn-off time	tq	1J = 123 0	100	



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THERMAL AND MECHANICAL SPECIFICATIONS								
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS				
Maximum junction and storage temperature range	T _J , T _{Stg}		-40 to +125	°C				
Maximum thermal resistance, junction to case	R _{thJC}	DC operation	1.5					
Maximum thermal resistance, junction to ambient	R _{thJA}		62	°C/W				
Typical thermal resistance, case to heatsink	R _{thCS}	Mounting surface, smooth, and greased	0.5					
Approximate weight			2	g				
Approximate weight			0.07	oz.				
Mounting torque	minimum		6 (5)	kgf · cm				
	maximum		12 (10)	(lbf · in)				
Marking device		Case style TO-220AB	12TT	S08H				

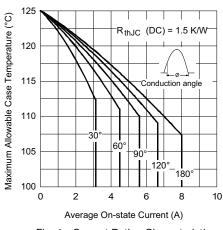
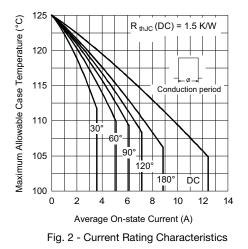


Fig. 1 - Current Rating Characteristics



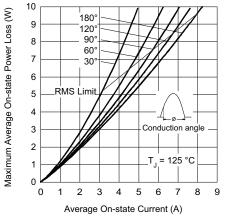


Fig. 3 - On-State Power Loss Characteristics

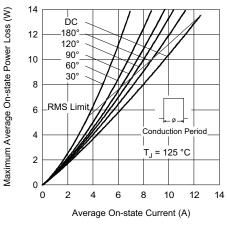
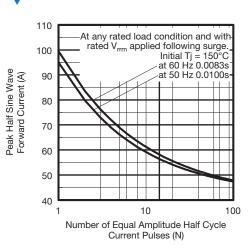


Fig. 4 - On-State Power Loss Characteristics

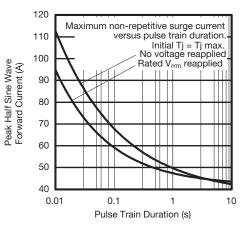
VS-12TTS08HM3

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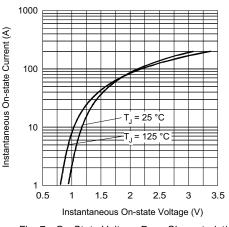


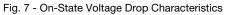
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Fig. 5 - Maximum Non-Repetitive Surge Current









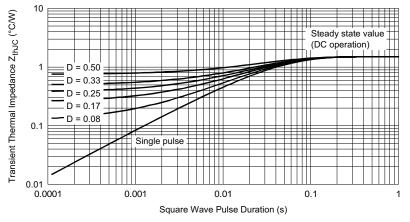


Fig. 8 - Thermal Impedance Z_{thJC} Characteristics

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ORDERING INFORMATION TABLE

Device code	VS-	12	т	т	S	08	н	М3
		2	3	4	5	6	7	8
	1.	- Visl	hay Sen	nicondu	ctors pro	oduct		
	2 -	- Cur	rent rati	ng (12.5	5 A)			
	3 -	- Circ	cuit conf	iguratio	า:			
		T =	single t	nyristor				
	4 -	· Pac	kage:					
	_	T =	TO-220					
	5 -	. Тур	e of silio	con:				
		S =	standa	d recov	ery rect	ifier		
	6 -	· Vol	tage rati	ng (08 =	= 800 V))		
	7 -	• H=	AEC-Q	101 qua	lified			
	8	- Env	vironmer	ntal digit	:			
		М3	= halog	en-free,	RoHS-0	complia	nt, and	termina

ORDERING INFORMATION (Example)									
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION						
VS-12TTS08HM3	50	1000	Antistatic plastic tube						

LINKS TO RELATED DOCUMENTS						
Dimensions www.vishay.com/doc?95222						
Part marking information	www.vishay.com/doc?95028					

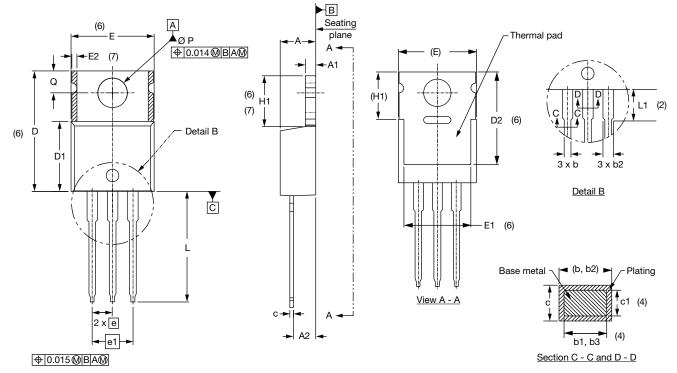
Outline Dimensions



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TO-220AB

DIMENSIONS in millimeters and inches



Lead tip

reten Teten reten

Conforms to JEDEC[®] outline TO-220AB

SYMBOL	MILLIN	MILLIMETERS INC		HES	NOTES		SYMBOL	MILLIN	IETERS	INC	HES	NOTES
STIVIDUL	MIN.	MAX.	MIN.	MAX.	NOTES		STIVIDUL	MIN.	MAX.	MIN.	MAX.	NOTES
А	4.25	4.65	0.167	0.183			D2	11.68	12.88	0.460	0.507	6
A1	1.14	1.40	0.045	0.055			E	10.11	10.51	0.398	0.414	3, 6
A2	2.56	2.92	0.101	0.115			E1	6.86	8.89	0.270	0.350	6
b	0.69	1.01	0.027	0.040			E2	-	0.76	-	0.030	7
b1	0.38	0.97	0.015	0.038	4		е	2.41	2.67	0.095	0.105	
b2	1.20	1.73	0.047	0.068			e1	4.88	5.28	0.192	0.208	
b3	1.14	1.73	0.045	0.068	4		H1	5.84	6.86	0.230	0.270	6, 7
С	0.36	0.61	0.014	0.024			L	13.52	14.02	0.532	0.552	
c1	0.36	0.56	0.014	0.022	4		L1	3.32	3.82	0.131	0.150	2
D	14.85	15.25	0.585	0.600	3		ØР	3.54	3.73	0.139	0.147	
D1	8.38	9.02	0.330	0.355			Q	2.60	3.00	0.102	0.118	

Notes

⁽¹⁾ Dimensioning and tolerancing as per ASME Y14.5M-1994

⁽²⁾ Lead dimension and finish uncontrolled in L1

(3) Dimension D, D1 and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body

⁽⁴⁾ Dimension b1, b3 and c1 apply to base metal only

⁽⁵⁾ Controlling dimensions: inches

⁽⁶⁾ Thermal pad contour optional within dimensions E, H1, D2 and E1

- ⁽⁷⁾ Dimensions E2 x H1 define a zone where stamping and singulation irregularities are allowed
- (8) Outline conforms to JEDEC[®] TO-220, except A2 (maximum) and D2 (minimum) where dimensions are derived from the actual package outline

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